

IN THE CLAIMS:

1. to 12. (Cancelled)

13. (New) A magnetic memory comprising a magnetoresistive film comprising:

a first magnetic layer comprising a perpendicular magnetization film;  
a second magnetic layer comprising a perpendicular magnetization film having a higher coercive force than that of said first magnetic layer;  
a nonmagnetic layer arranged between said first magnetic layer and said second magnetic layer; and  
a switch element connected to said first magnetic layer or said second magnetic layer.